WNSC2D501200W

Silicon Carbide Diode

Rev.02 - 1 April 2024 Product data sheet

1. General description

Silicon Carbide Schottky diode in a TO247-2L plastic package, designed for high frequency switched-mode power supplies.

RoHS Halogen-Free Lead-Free

2. Features and benefits

- Highly stable switching performance
- High forward surge capability I_{FSM}
- Extremely fast reverse recovery time
- Superior in efficiency to Silicon Diode alternatives
- Reduced losses in associated MOSFET
- Reduced EMI
- Reduced cooling requirements
- RoHS compliant
- High junction operating temperature capability ($T_{j(max)}$ = 175 °C)

3. Applications

- Power factor correction
- UPS & energy storage systems
- PV MPPT circuit
- 3-level rectifier and inverters

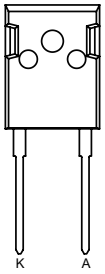
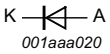
4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Notes	Values			Unit
Absolute maximum rating							
V_{RRM}	repetitive peak reverse voltage			1200			V
I_F	continuous forward current	T_{mb} ≤ 126 °C, DC; Fig. 2		50			A
T_j	junction temperature			-55 to 175			°C
Symbol	**Parameter**	**Conditions**	**Notes**	**Min**	**Typ**	**Max**	**Unit**
Static characteristics							
V_F	forward voltage	I_F = 50 A; T_j = 25 °C; Fig. 5		-	1.42	1.60	V
		I_F = 50 A; T_j = 150 °C; Fig. 5		-	1.90	2.30	V
		I_F = 50 A; T_j = 175 °C; Fig. 5		-	2.00	2.50	V
Dynamic characteristics							
Q_r	recovered charge	I_F = 50 A; dI_F/dt = 500 A/µs; V_R = 400 V; T_j = 25 °C; Fig. 7		-	125	-	nC

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	 TO247-2L	 *001aaa020*
2	A	anode		
mb	mb	mounting base; connected to cathode		

6. Ordering information

Table 3. Ordering information

Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
WNSC2D501200W	TO247-2L	WNSC2D501200W6Q	Tube	30	TO247L-2L(L)	10-Nov-2020
					TO247P-2L(P)	31-Mar-2023

7. Marking

Table 4. Marking codes

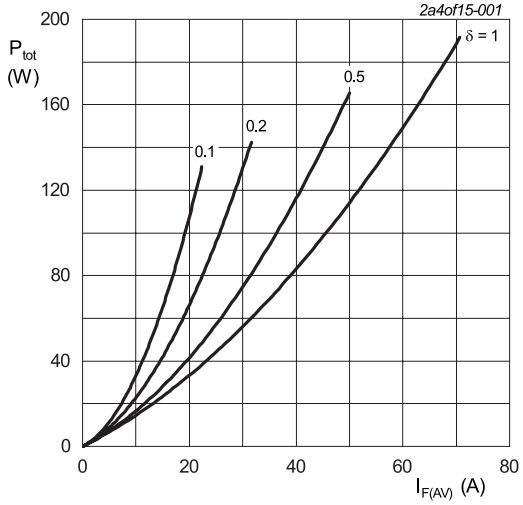
Type number	Marking codes
WNSC2D501200W	WNSC2D 501200W

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Values	Unit
V_{RRM}	repetitive peak reverse voltage			1200	V
V_{RWM}	crest working reverse voltage			1200	V
V_R	reverse voltage	DC		1200	V
I_F	continuous forward current	$T_{mb} \leq 126$ °C, DC; Fig. 2		50	A
		$T_{mb} \leq 125$ °C, DC; Fig. 2		51	A
		$T_{mb} \leq 25$ °C, DC; Fig. 2		105	A
I_{FRM}	repetitive peak forward current	$\delta = 0.5$; $t_p = 25$ µs; $T_{mb} \leq 125$ °C; square-wave pulse		81	A
I_{FSM}	non-repetitive peak forward current	$t_p = 10$ ms; $T_{j(init)} = 25$ °C; sine-wave pulse		420	A
		$t_p = 10$ µs; $T_{j(init)} = 25$ °C; square-wave pulse		2400	A
I^2t	I^2t for fusing	sine-wave pulse; $T_{j(init)} = 25$ °C; $t_p = 10$ ms		882	A^2s
T_{stg}	storage temperature			-55 to 175	°C
T_j	junction temperature			-55 to 175	°C



$I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$

$V_o = 1.252$ V; $R_s = 0.0206$ Ω

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

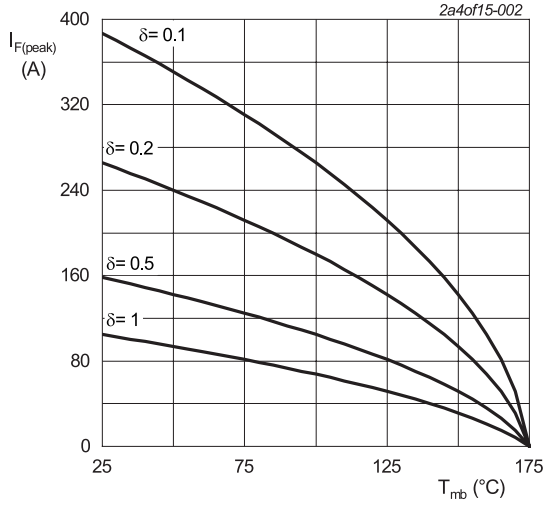


Fig. 2. Current derating as a function of mounting base temperature

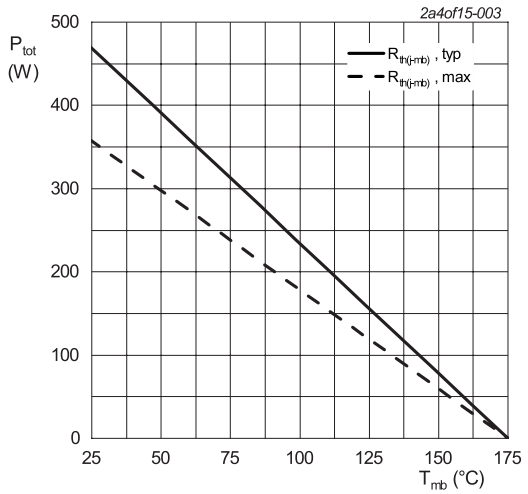


Fig. 3. Total power dissipation as a function of mounting base temperature

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 4		-	0.32	0.42	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air		-	40	-	K/W

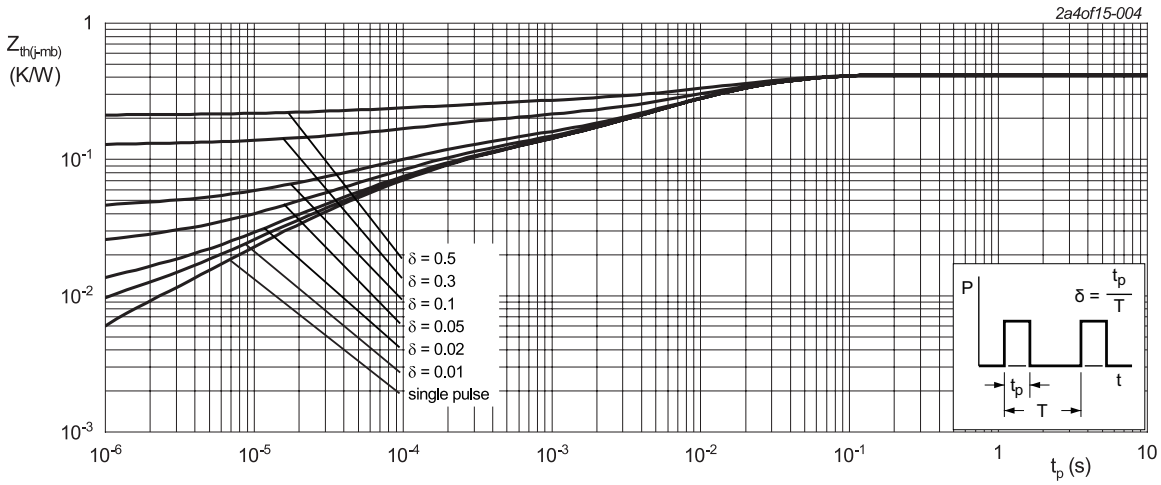
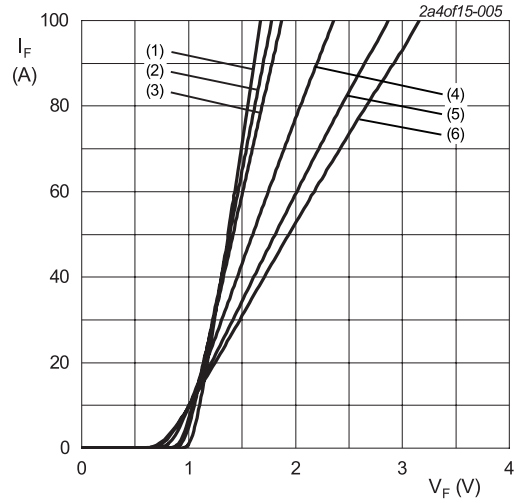


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
Static characteristics							
V_F	forward voltage	I_F = 50 A; T_j = 25 °C; Fig. 5		-	1.42	1.60	V
		I_F = 50 A; T_j = 150 °C; Fig. 5		-	1.90	2.30	V
		I_F = 50 A; T_j = 175 °C; Fig. 5		-	2.00	2.50	V
I_R	reverse current	V_R = 1200 V; T_j = 25 °C; Fig. 6		-	1.5	250	µA
		V_R = 1200 V; T_j = 175 °C; Fig. 6		-	50	-	µA
Dynamic characteristics							
Q_r	recovered charge	I_F = 50 A; V_R = 400 V; dI_F/dt = 500 A/µs; T_j = 25 °C; Fig. 7		-	125	-	nC
C_d	diode capacitance	f = 1 MHz; V_R = 1 V; T_j = 25 °C		-	2522	-	pF
		f = 1 MHz; V_R = 400 V; T_j = 25 °C		-	221	-	pF
		f = 1 MHz; V_R = 800 V; T_j = 25 °C		-	158	-	pF
E_{as}	non-repetitive avalanche energy	I_R = 10.4 A; L = 10 mH; $T_{j(init)}$ = 25 °C		540	-	-	mJ



V_o = 1.252 V; R_s = 0.0206 Ω
(1) T_j = -55 °C; typical values
(2) T_j = 0 °C; typical values
(3) T_j = 25 °C; typical values
(4) T_j = 100 °C; typical values
(5) T_j = 150 °C; typical values
(6) T_j = 175 °C; typical values

Fig. 5. Forward current as a function of forward voltage; typical values

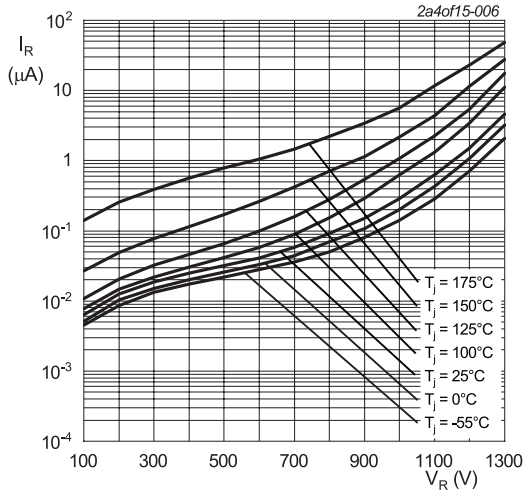


Fig. 6. Reverse leakage current as a function of reverse voltage; typical value

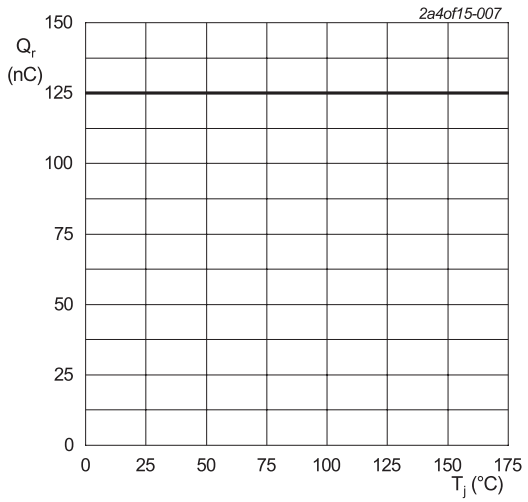
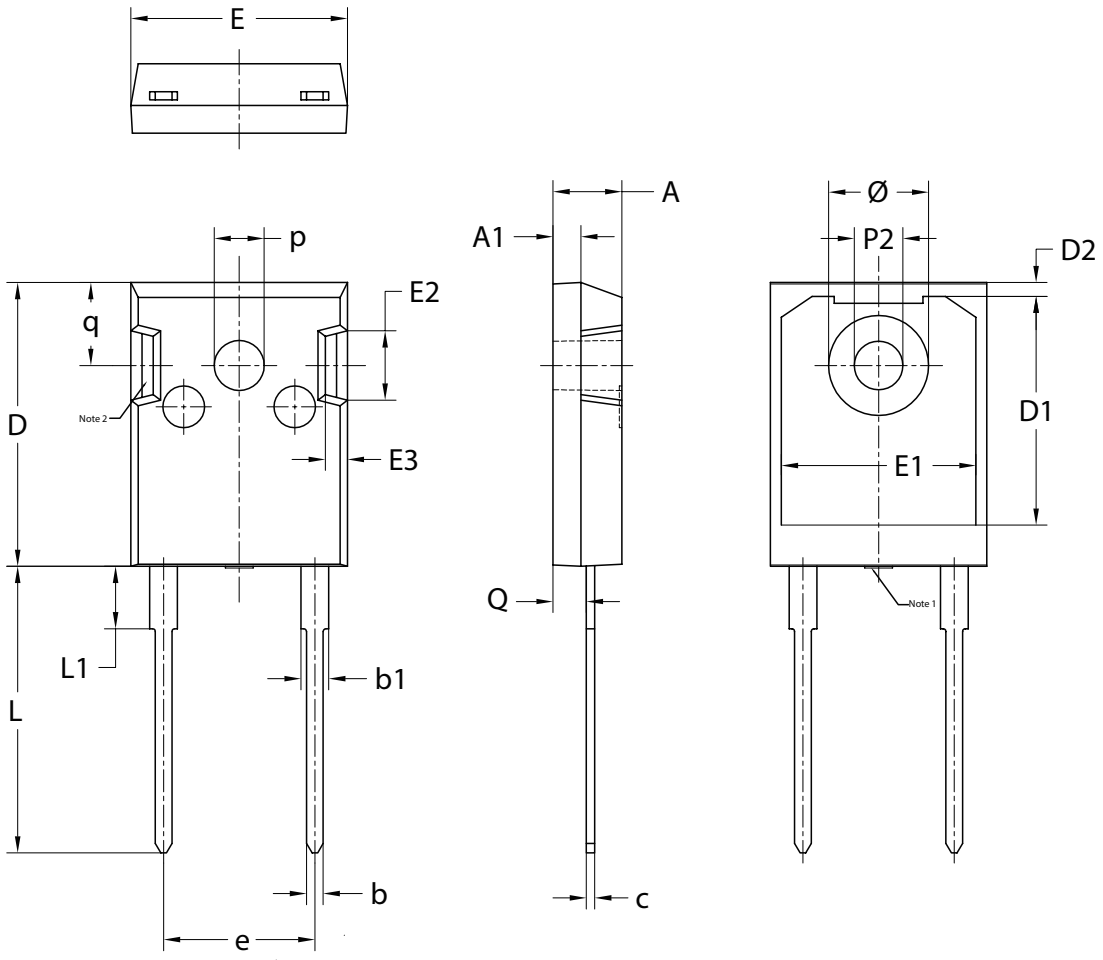


Fig. 7. Recovered charge as a function of junction temperature

11. Package outline

Plastic single-ended through-hole package; heatsink mounted;1 mounting hole; 2 leads TO-247 TO247-2L



UNIT	A	A_1	b	b_1	c	D	D_1 (2)	D_2	E	E_1	E_2	E_3	e	L	L_1	P_2	p	Q	q	Ø
mm	5.20 4.70	2.10 1.90	1.40 1.00	2.20 1.80	0.70 0.50	20.60 20.30	16.20 16.87	1.20 0.80	15.75 15.45	14.22 13.82	5.20 4.80	1.80 1.40	10.90 BSC	20.72 20.22	4.75 4.25	3.60 3.40	3.70 3.50	2.60 2.20	6.18 5.78	7.30 7.10

Note:
1. Mold resin protrusion max 0.127mm.
2. Metal exposed with Sn plating.

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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